

In response to the Office action dated August 15, 2002, please amend the above identified application as follows.

IN THE CLAIMS:

Please amend the claims as follows:

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1 2. (Twice amended) Monoatomic and monocrystalline
2 layer according to claim 1, the SiC monocrystalline
3 substrate being a thin layer of monocrystalline SiC in
4 cubic phase β -SiC (100) formed on a platelet of Si, the
5 monoatomic and monocrystalline layer thus closely
6 covering the totality of this platelet.

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1 6. (Twice amended) Process according to claim 5, in
2 which the SiC monocrystalline substrate is prepared from
3 a thin layer of monocrystalline SiC in cubic phase β -SiC
4 with a face (100) terminated by a layer of Si.

1 7. (Twice amended) Process according to claim 5, in
2 which the SiC monocrystalline substrate is prepared from
3 a monocrystalline SiC platelet in hexagonal phase with a
4 face (1000) terminated by a layer of Si.

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1 11. (Twice amended) Process according to claim 5,
2 in which, to transform the plane of carbon-carbon dimers
3 of sp configuration into a plane of carbon-carbon dimers

B3 end

4 of sp^3 configuration, one carries out an annealing or a
5 plurality of successive annealings, at a temperature
6 approximately equal to $1250^{\circ}C$, of the monocrystalline
7 substrate in SiC terminated by the atomic plane of carbon
8 according to the reconstruction $c(2 \times 2)$, the total time of
9 annealing being greater than or about equal to 25
10 minutes.

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1 12. (Amended) Process according to claim 7, in
2 which, to obtain the atomic plane of carbon according to
3 the reconstruction $c(2 \times 2)$, an annealing is carried out
4 capable of eliminating the layer of Si.
